

## References:

- [1] M. Takabatake, J. Ohwada, Y. A. Ono, K. Ono, A. Mimura, N. Konishi, "CMOS circuits for peripheral circuit integrated poly-Si TFT LCD fabricated at low temperature below 600 degrees C," *IEEE Trans. Electron Devices*, vol. 38, pp. 1303-1309, 1991.
- [2] Nobuo Kubo, Naoto Kusumoto, Takashi, Inushima, and Shumpei Yamazaki. "Characteristics of Polycrystallize Si Thin Film Transistors Fabricated by Excimer Laser Annealing Method" *IEEE TRANSACTIONS ON ELECTRON DEVICES*.VOL.41.NO.10.OCTOBER 1994.
- [3] Takashi Noguchi, Andrew J. Tang, Julie A. Tsai, Member, IEEE, and Rafael Reif, Fellow IEEE. "Comparison of Effects Between Large-Area-Beam ELA and SPC on TFT characteristics" *IEEE TRANSACTIONS ON ELECTRON DEVICES*.VOL.43.NO.9.SEPTEMBER 1996.
- K.Sera, F.Okumura, H.Uchoda, S.Itoh, S.Kaneko, and K.Hotta. "High-performance TFT'S fabricated by XeCl excimer laser annealing of hydrogenated amorphous-silicon film" *IEEE ELECTRON DEVICES*.VOL ED-36, P.2868,1989.
- [4] Shengdong Zhang, Chunxiang Zhu, Johnny K. O. Sin, J. N. Li, and Philip K. T. Mok, "Ultra-thin elevated channel poly-Si TFT technology for fully-integrated AMLCD system on glass," *IEEE Trans. Electron Devices*, vol. 47, pp. 569-575, 2000.
- [5] A. Nakamura, F. Emoto, E. Fujji, Y. Uemoto, A. Yamamoto, K. Senda, and G. Kano, "Recrystallization mechanism for solid phase growth of poly-Si films on quartz substrate," *Jpn. J. Appl. Phys. Part2*, vol. 27, pp. L2408-L2410, 1988.
- [6] S. Uchikoga and N. Ibaraki, "Low temperature poly-Si TFT-LCD by excimer laser anneal," *Thin Solid Films*, vol. 383, pp. 19-24, 2001.

- [7] M Vopsaroiu, G Vallejo Fernandez, M J Thwaites, J Anguita, P J Grundy and K O'Grady  
Deposition of polycrystalline thin films with controlled grain size  
2005 *J. Phys. D: Appl. Phys.* 38 490-496
- [8] Krishnan, A.T.; Sanghoon Bae; Fonash, S.J.;*Electron Device Letters*,"Fabrication of microcrystalline silicon TFTs using a high-density plasma approach", IEEE  
Volume 22, Issue 8, Aug. 2001 Page(s):399 - 401
- [9] AUO LTPS group paper 2004.
- [10] T.Sameshima, and S.Usui, *Appl. Phys. Lett.* 59 , 2724 (1991)
- [11] T.Sameshima, and S.Usui, *Mat. Res. Soc. Symp. Proc.* Vol. 258
- [12] James S. Im and H. J. Kim, "On the super lateral growth phenomenon observed in excimer laser-induced crystallization of thin Si films," *Appl. Phys. Lett.*, vol. 64, pp. 2303-2305, 1994.
- [13] Huang-Chung Cheng, Ya-Hsiang Tai, Ming-Shiann Feng, Jau-Jey Wang, "Characteristics of polycrystalline silicon thin-film transistors with thin oxide/nitride gate structures ,"  
*OPTICAL ENGINEERING*, vol. 32, no.8, 1798.
- [14] T.Sameshima, and S.Usui, *Appl. Phys. Lett.* 59 , 2724 (1991)
- [15] S. Wolf and R.N. Tauber, (*Silicon Processing for the VLSI*, Vol.1, Sunset Beach, California, Lattice Press, 1986), 533
- [16] S. R. Stiffler, Michael O. Thompson, and P. S. Peercy, "Supercooling and nucleation of silicon after laser melting," *Phys. Rev. Lett.*, vol. 60, pp. 2519-2522, 1988.
- [17] G Y. Kuo and P.M. Koziowski, *Appl. Phys. Lett.* **69**, 1092 (1996)
- [18] M. Furuta, T. Kawamura, T. Yoshioka and Y. Miyata, *IEEE Trans. Electron Devices* **40**, 1964 (1993)
- [19] S.D.S. Malhi, H. Shichijo, S. K. Banerjee, M. Elahy, G.P. Pollack, W.F. Richardson, A.H. Shah, L.R. Hite, R.H. Womack, P.K. Chatterjee and H.W. Lam, *IEEE Trans. Electron Devices* **ED-32**, 258 (1985)

- [20] H.J. Lim, B.Y. Ryu and J. Jang, *Appl. Phys. Lett.* **66**, 2888 (1995) [30] K. Sera, F. Okumura, H. Uchida, S. Itoh, S. Kaneko, K. Hotta, *IEEE Trans. Electron Devices* **36**, 2868 (1989)
- [21] Apostolos T. Voutsas, Aaron M. Marmorstein, and Raj Solanki, “ The impact of annealing ambient on the performance of excimer-laser-annealed polysilicon thin-film transistors,” *J. Electrochem. Soc.*, vol. 146, pp. 3500-3505, 1
- [22] Y. Helen, R. Dassow, M. Nerding, K. Mourgues, F. Raoult, J.R. Kohler, T. Mohammed-Brahim, R. Rogel, O. Bonnaud, J.H. Werner, and H.P. Strunk, “High mobility thin film transistors by Nd:YVO4-laser crystallization,” *Thin Solid Films*, vol. 383, pp. 143-146, 2001.
- [23] E-CON TECHNOLOGY.CO.LTD, 2001.

